

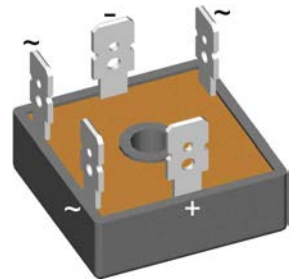
Standard Rectifier Module

3~ Rectifier	
V_{RRM}	= 1200 V
I_{DAV}	= 27 A
I_{FSM}	= 550 A

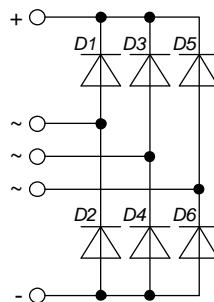
3~ Rectifier Bridge

Part number

VUO36-12N08



 E72873



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very low forward voltage drop
- Improved thermal behaviour

Applications:

- Diode for main rectification
- For three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Package: FO-B

- Isolation Voltage: 3000 V~
- Industry standard outline
- RoHS compliant
- 1/4" fast-on terminals
- Easy to mount with one screw

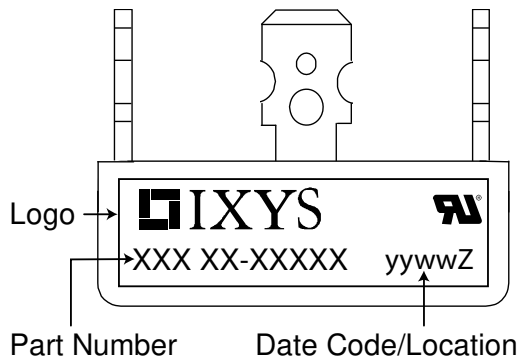
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Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage					1300	V
V_{RRM}	max. repetitive reverse blocking voltage					1200	V
I_R	reverse current	$V_R = 1200\text{ V}$		$T_{VJ} = 25^\circ\text{C}$		40	μA
		$V_R = 1200\text{ V}$		$T_{VJ} = 150^\circ\text{C}$		1,5	mA
V_F	forward voltage drop	$I_F = 15\text{ A}$		$T_{VJ} = 25^\circ\text{C}$		1,04	V
		$I_F = 45\text{ A}$				1,23	V
		$I_F = 15\text{ A}$		$T_{VJ} = 125^\circ\text{C}$		0,93	V
		$I_F = 45\text{ A}$				1,18	V
I_{DAV}	bridge output current	$T_C = 85^\circ\text{C}$		$T_{VJ} = 150^\circ\text{C}$		27	A
		rectangular	$d = \frac{1}{3}$				
V_{FO}	threshold voltage			$T_{VJ} = 150^\circ\text{C}$		0,76	V
r_F	slope resistance					9,1	m Ω
						} for power loss calculation only	
R_{thJC}	thermal resistance junction to case					7	K/W
R_{thCH}	thermal resistance case to heatsink				1		K/W
P_{tot}	total power dissipation			$T_C = 25^\circ\text{C}$		17	W
I_{FSM}	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$		$T_{VJ} = 45^\circ\text{C}$		550	A
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$		$V_R = 0\text{ V}$		595	A
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$		$T_{VJ} = 150^\circ\text{C}$		470	A
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$		$V_R = 0\text{ V}$		505	A
I^2t	value for fusing	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$		$T_{VJ} = 45^\circ\text{C}$		1,52	kA ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$		$V_R = 0\text{ V}$		1,48	kA ² s
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$		$T_{VJ} = 150^\circ\text{C}$		1,11	kA ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$		$V_R = 0\text{ V}$		1,06	kA ² s
C_J	junction capacitance	$V_R = 400\text{ V}; f = 1\text{ MHz}$		$T_{VJ} = 25^\circ\text{C}$		18	pF



Package FO-B		Ratings				
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			100	A
T_{VJ}	virtual junction temperature		-40		150	°C
T_{op}	operation temperature		-40		125	°C
T_{stg}	storage temperature		-40		125	°C
Weight				20		g
M_D	mounting torque		1,8		2,2	Nm
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	9,0	7,0		mm
$d_{Spb/Apb}$		terminal to backside	10,0	10,0		mm
V_{ISOL}	isolation voltage	t = 1 second t = 1 minute	3000 2500			V V
		50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA				

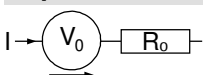


Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	VUO36-12NO8	VUO36-12NO8	Box	50	465143

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 150^{\circ}C$

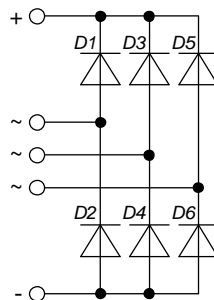
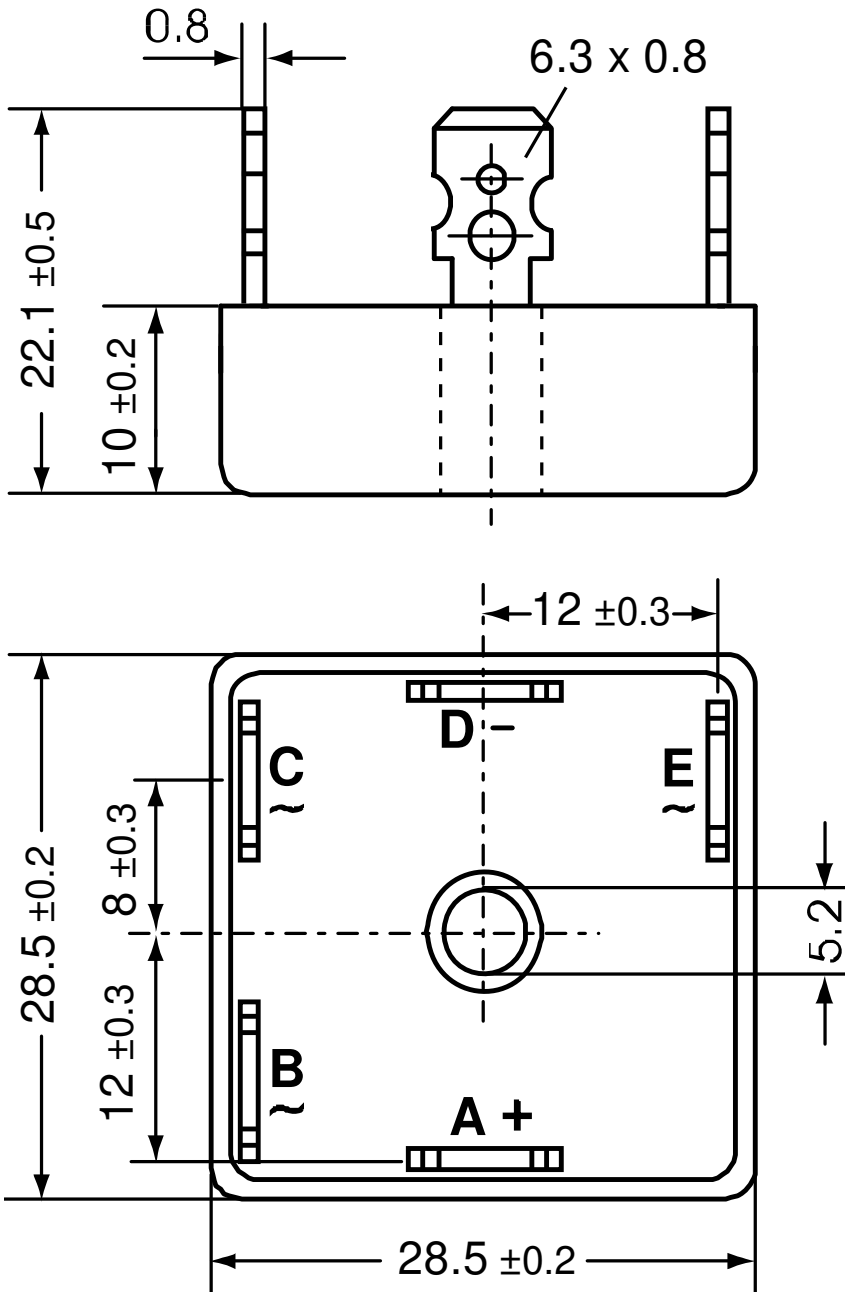


Rectifier

$V_{0\ max}$	threshold voltage	0,76	V
$R_{0\ max}$	slope resistance *	7,9	mΩ



Outlines FO-B



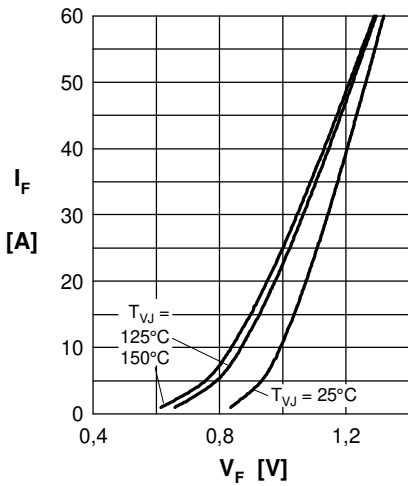
Rectifier


Fig. 1 Forward current vs. voltage drop per diode

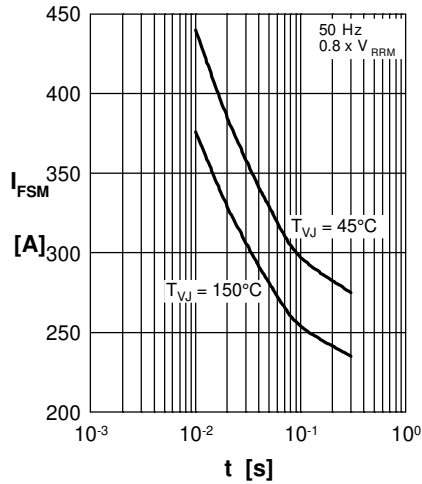


Fig. 2 Surge overload current vs. time per diode

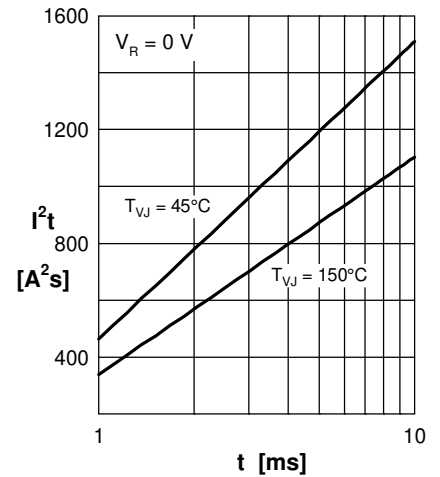
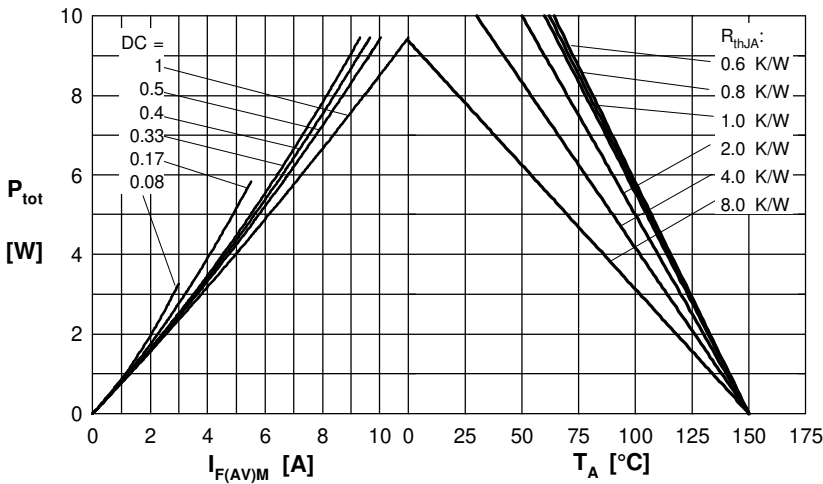

 Fig. 3 I^2t vs. time per diode


Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

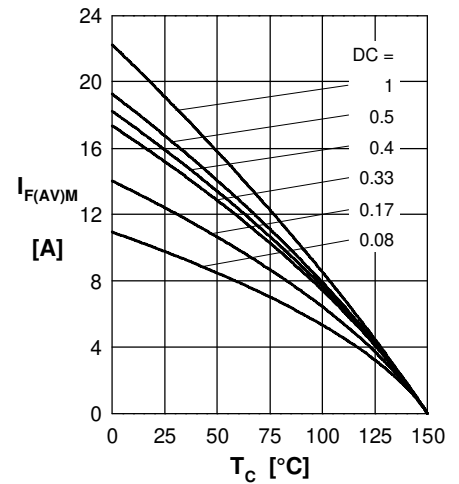


Fig. 5 Max. forward current vs. case temperature per diode

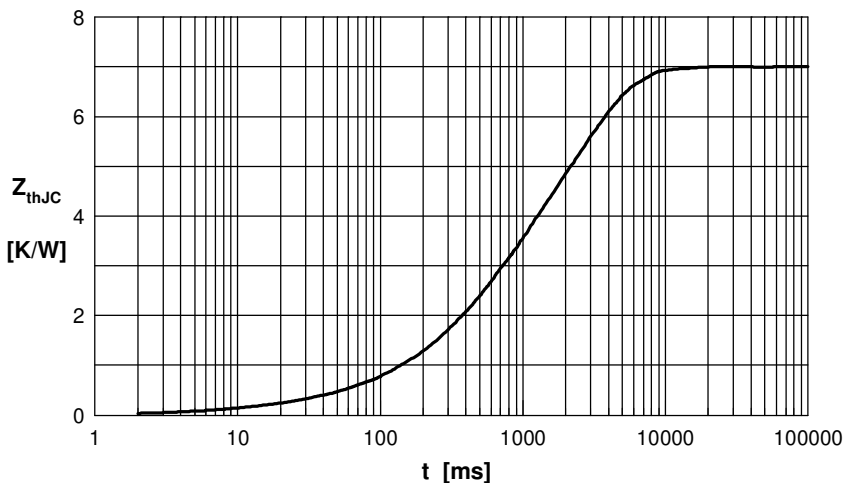


Fig. 6 Transient thermal impedance junction to case vs. time per diode

 Constants for Z_{thJC} calculation:

i	R_{th} (K/W)	t_i (s)
1	0.040	0.005
2	0.150	0.030
3	1.710	0.400
4	5.100	2.300